IN THE CLAIMS:

1. (Currently Amended) A method of manufacturing a display device comprising:

forming a thin film transistor over a substrate;

forming an electrode which is electrically connected with the thin film transistor; and

forming a thin film over the electrode with an electron beam evaporation method,

wherein an acceleration voltage of electrons of the electron beam evaporation method is controlled such that ~~radial rays are not substantially~~ the thin film transistor is not deteriorated with radial rays radiated from an evaporation material for forming the thin film when the evaporation material is irradiated with an electron beam[[.]], and

wherein increase of a sub-threshold coefficient of the thin film transistor is prevented by controlling the acceleration voltage of electrons.

2. (Previously Presented) A method of manufacturing a display device comprising:

forming a thin film transistor over a substrate;

forming an electrode which is electrically connected with the thin film transistor; and

forming a thin film over the electrode with an electron beam evaporation method,

wherein an acceleration voltage of electrons of the electron beam evaporation method is controlled such that the thin film transistor is not deteriorated with radial rays radiated from an evaporation material for forming the thin film when the evaporation material is irradiated with an electron beam.

3. (Currently Amended) A method of manufacturing a display device comprising:

forming a thin film transistor over a substrate;

forming a first electrode which is electrically connected with the thin film transistor;

forming a light emitter containing an organic compound over the first electrode; and

forming a second electrode over the light emitter with an electron beam evaporation method,

wherein an acceleration voltage of electrons of the electron beam evaporation method is controlled such that ~~radial rays are not substantially~~ the thin film transistor is not deteriorated with radial rays radiated from an evaporation material for forming the second electrode when the evaporation material is irradiated with an electron beam[[.]], and

wherein increase of a sub-threshold coefficient of the thin film transistor is prevented by controlling the acceleration voltage of electrons.

4. (Previously Presented) A method of manufacturing a display device comprising:

forming a thin film transistor over a substrate;

forming a first electrode which is electrically connected with the thin film transistor;

forming a light emitter containing an organic compound over the first electrode; and

forming a second electrode over the light emitter with an electron beam evaporation method,

wherein an acceleration voltage of electrons of the electron beam evaporation method is controlled such that the thin film transistor is not deteriorated with radial rays radiated from the evaporation material for forming the second electrode when the evaporation material is irradiated with an electron beam.

5. (Currently Amended) A method of manufacturing a display device comprising:

forming a thin film transistor over a substrate;

forming an electrode which is electrically connected with the thin film transistor; and

forming a thin film over the electrode with an electron beam evaporation method,

wherein a thickness of the thin film is 0.1 μm or less, and

wherein control is performed such that a time during which the thin film transistor is exposed to radial rays radiated from an evaporation material for forming the thin film, is shortened ~~with a thickness of the thin film of 0.1 μm or less~~ to ~~thereby~~ avoid deterioration of the thin film transistor when the evaporation material is irradiated with an electron beam.

6. (Currently Amended) A method of manufacturing a display device

comprising:

forming a thin film transistor over a substrate;

forming a first electrode which is electrically connected with [[a]] the thin film transistor;

forming a light emitter containing an organic compound over the first electrode; and

forming a second electrode over the light emitter with an electron beam evaporation method,

wherein a thickness of the second electrode is 0.1 μm or less, and

wherein control is performed such that a time during which the thin film transistor is exposed to radial rays radiated from an evaporation material for forming the second electrode, is shortened ~~with a thickness of the second electrode of 0.1 μm or less~~ to ~~thereby~~ avoid deterioration of the thin film transistor when the evaporation material is irradiated with an electron beam.

7. (Original) A method of manufacturing a display device according to claim 1, wherein a multi-component alloy or compound, which is constituted of a metal component and a component containing either or both of alkali metal and alkali earth metal, is used as the evaporation material.

8. (Original) A method of manufacturing a display device according to claim 2, wherein a multi-component alloy or compound, which is constituted of a metal component and a component containing either or both of alkali metal and alkali earth metal, is used as the evaporation material.

9. (Original) A method of manufacturing a display device according to claim 3, wherein a multi-component alloy or compound, which is constituted of a metal component and a component containing either or both of alkali metal and alkali earth metal, is used as the evaporation material.

10. (Original) A method of manufacturing a display device according to claim 4, wherein a multi-component alloy or compound, which is constituted of a metal component

and a component containing either or both of alkali metal and alkali earth metal, is used as the evaporation material.

11. (Original) A method of manufacturing a display device according to claim 5, wherein a multi-component alloy or compound, which is constituted of a metal component and a component containing either or both of alkali metal and alkali earth metal, is used as the evaporation material.

12. (Original) A method of manufacturing a display device according to claim 6, wherein a multi-component alloy or compound, which is constituted of a metal component and a component containing either or both of alkali metal and alkali earth metal, is used as the evaporation material.

Please add the following new claims:

13. (New) A method of manufacturing a display device according to claim 1, wherein radial rays are not substantially radiated from the evaporation material for forming the thin film when the evaporation material is irradiated with the electron beam.

14. (New) A method of manufacturing a display device according to claim 2, wherein radial rays are not substantially radiated from the evaporation material for forming the thin film when the evaporation material is irradiated with the electron beam.

15. (New) A method of manufacturing a display device according to claim 3, wherein radial rays are not substantially radiated from the evaporation material for forming the thin film when the evaporation material is irradiated with the electron beam.

16. (New) A method of manufacturing a display device according to claim 4, wherein radial rays are not substantially radiated from the evaporation material for forming the thin film when the evaporation material is irradiated with the electron beam.